

# **FDS4480**

## **40V N-Channel PowerTrench® MOSFET**

### **General Description**

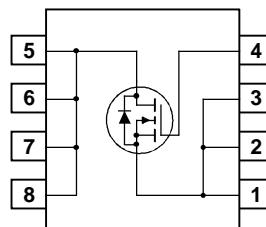
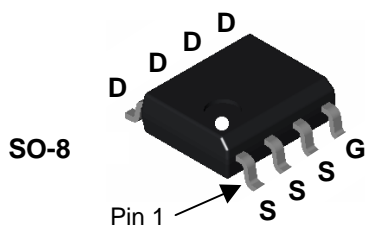
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $R_{DS(ON)}$  and fast switching speed.

### **Applications**

- DC/DC converter

### **Features**

- 10.8 A, 40 V.  $R_{DS(ON)} = 12\text{ m}\Omega$  @  $V_{GS} = 10\text{ V}$
- Low gate charge (29 nC)
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability



### **Absolute Maximum Ratings** $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	40	V
$V_{GSS}$	Gate-Source Voltage	+30/-20	V
$I_D$	Drain Current – Continuous (Note 1a)	10.8	A
	– Pulsed	45	
$P_D$	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.4	
		1.2	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ\text{C}$

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1c)	125	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	$^\circ\text{C/W}$

### **Package Marking and Ordering Information**

Device Marking	Device	Reel Size	Tape width	Quantity
FDS4480	FDS4480	13"	12mm	2500 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Drain-Source Avalanche Ratings** (Note 2)

$E_{AS}$	Drain-Source Avalanche Energy	Single Pulse, $V_{DD}=40\text{V}$ , $I_D=10.8\text{A}$			240	mJ
$I_{AS}$	Drain-Source Avalanche Current				10.8	A

**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$		42		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 30\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -20\text{ V}$ , $V_{DS} = 0\text{ V}$			-100	nA

**On Characteristics** (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3.9	5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$		-8		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 10.8\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 10.8\text{ A}$ , $T_J=125^\circ\text{C}$		8 13	12 21	m $\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 5\text{ V}$	22			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}$ , $I_D = 10.8\text{ A}$		36		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		1686		pF
$C_{oss}$	Output Capacitance			384		pF
$C_{rss}$	Reverse Transfer Capacitance			185		pF

**Switching Characteristics** (Note 2)

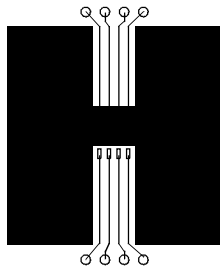
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 20\text{ V}$ , $I_D = 1\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		12	22	ns
$t_r$	Turn-On Rise Time			9	18	ns
$t_{d(off)}$	Turn-Off Delay Time			30	48	ns
$t_f$	Turn-Off Fall Time			15	27	ns
$Q_g$	Total Gate Charge	$V_{DS} = 20\text{ V}$ , $I_D = 10.8\text{ A}$ , $V_{GS} = 10\text{ V}$		29	41	nC
$Q_{gs}$	Gate-Source Charge			17		nC
$Q_{gd}$	Gate-Drain Charge			4		nC

Electrical Characteristics

T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain–Source Diode Characteristics and Maximum Ratings						
I <sub>S</sub>	Maximum Continuous Drain–Source Diode Forward Current				2.1	A
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.1 A (Note 2)		0.7	1.2	V
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 10.8 A, dI <sub>F</sub> /dt = 100 A/μs		27		nS
Q <sub>rr</sub>	Diode Reverse Recovery Charge			58		nC

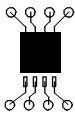
**Notes:**  
1. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.



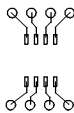
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

a) 50°C/W when mounted on a 1in<sup>2</sup> pad of 2 oz copper



b) 105°C/W when mounted on a .04 in<sup>2</sup> pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

## Typical Characteristics

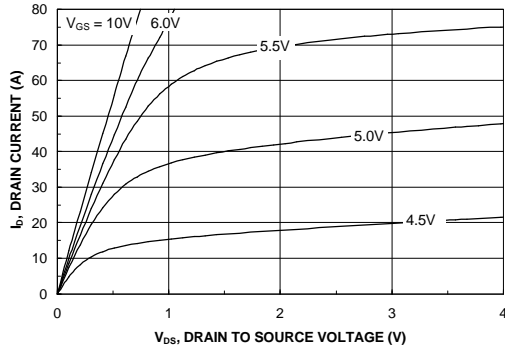


Figure 1. On-Region Characteristics.

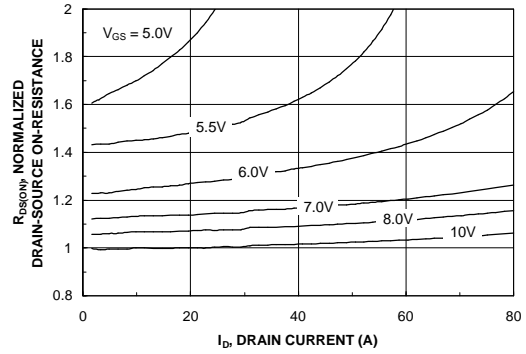


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

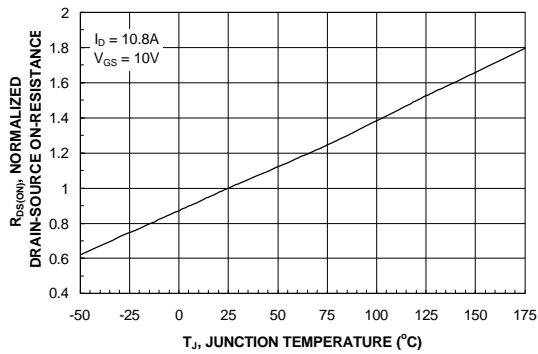


Figure 3. On-Resistance Variation with Temperature.

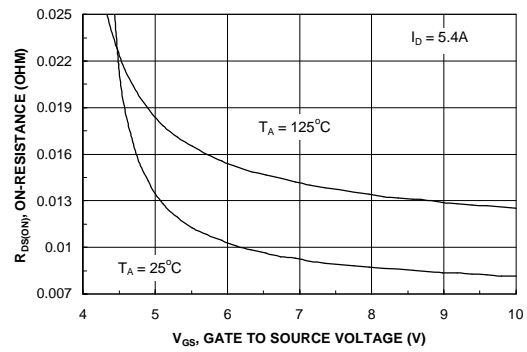


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

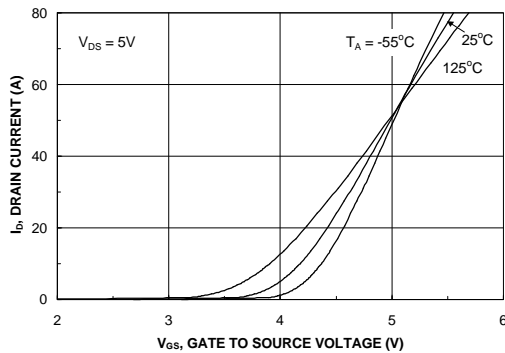


Figure 5. Transfer Characteristics.

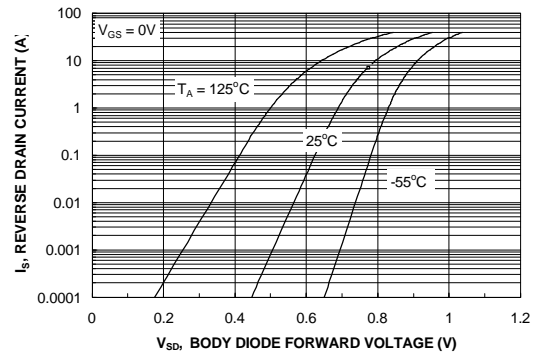


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

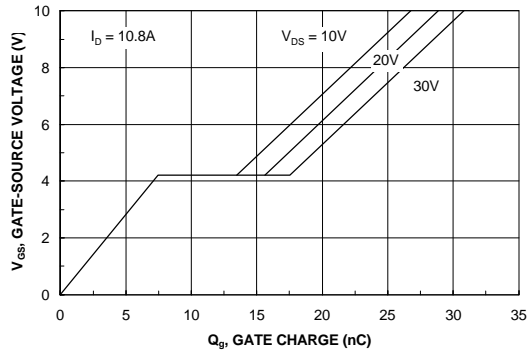


Figure 7. Gate Charge Characteristics.

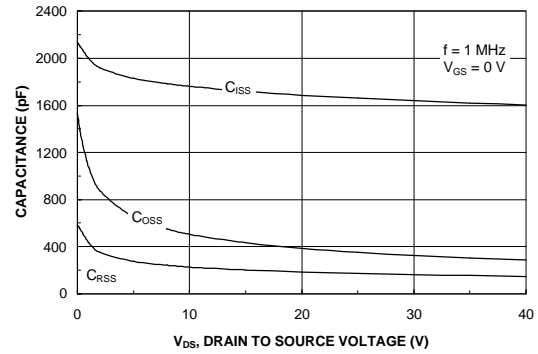


Figure 8. Capacitance Characteristics.

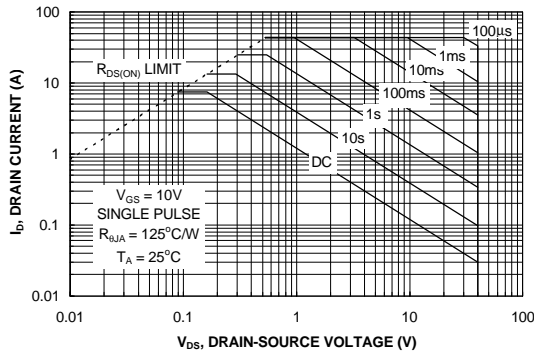


Figure 9. Maximum Safe Operating Area.

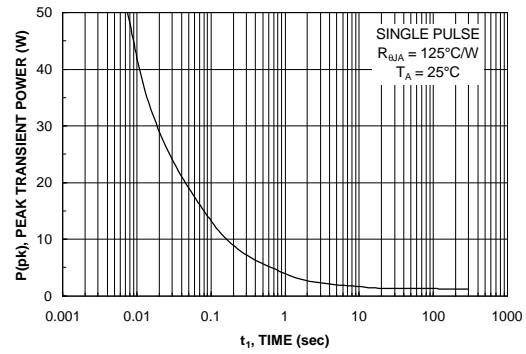


Figure 10. Single Pulse Maximum Power Dissipation.

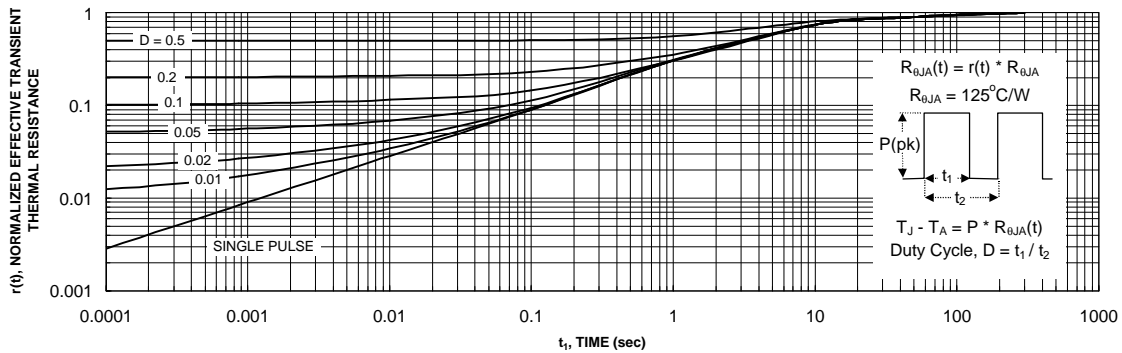


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

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